

N-Channel Enhancement Mode Power MOSFET

Description

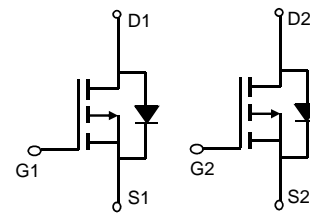
The HM2810D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a battery protection or in other switching application.

General Features

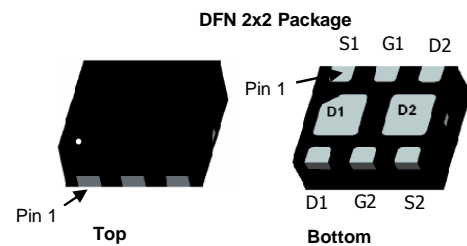
- $V_{DS} = 60V, I_D = 3.0A$
 $R_{DS(ON)} < 100m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 120m\Omega @ V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management



Schematic diagram



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM2810D	HM2810D	DFN2X2-6L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	3.0	A
		2.7	
Drain Current-Pulsed (Note 1)	I_{DM}	9.0	A
Maximum Power Dissipation	P_D	6.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.0	1.3	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =4.0 A	-	78	100	mΩ
		V _{GS} =4.5V, I _D =4.5A	-	84	120	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V,I _D =4A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =8V,V _{GS} =0V, F=1.0MHz	-	500	-	PF
Output Capacitance	C _{oss}		-	300	-	PF
Reverse Transfer Capacitance	C _{rss}		-	140	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V,I _D =1A V _{GS} =4.5V,R _{GEN} =6Ω	-	20	40	nS
Turn-on Rise Time	t _r		-	18	40	nS
Turn-Off Delay Time	t _{d(off)}		-	60	108	nS
Turn-Off Fall Time	t _f		-	28	56	nS
Total Gate Charge	Q _g	V _{DS} =10V,I _D =3A,V _{GS} =4.5V	-	10	15	nC
Gate-Source Charge	Q _{gs}		-	2.3	-	nC
Gate-Drain Charge	Q _{gd}		-	2.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	1	A

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

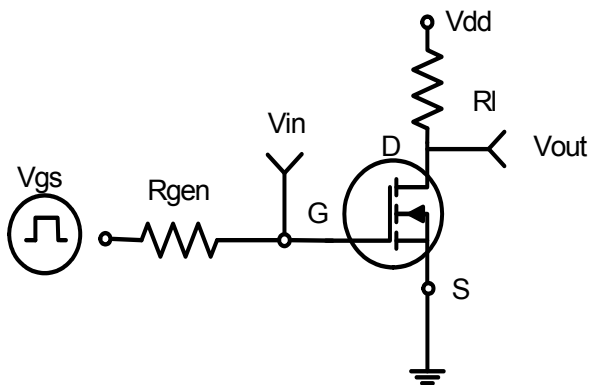


Figure 1: Switching Test Circuit

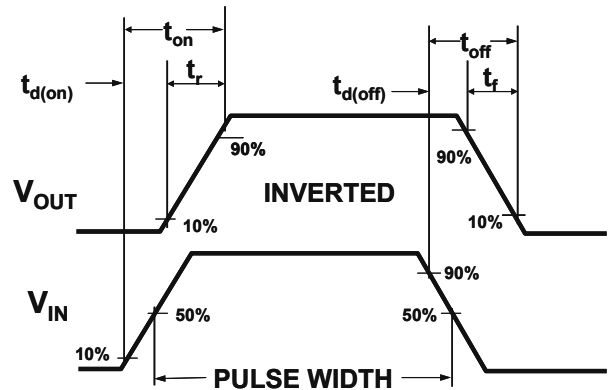


Figure 2: Switching Waveforms

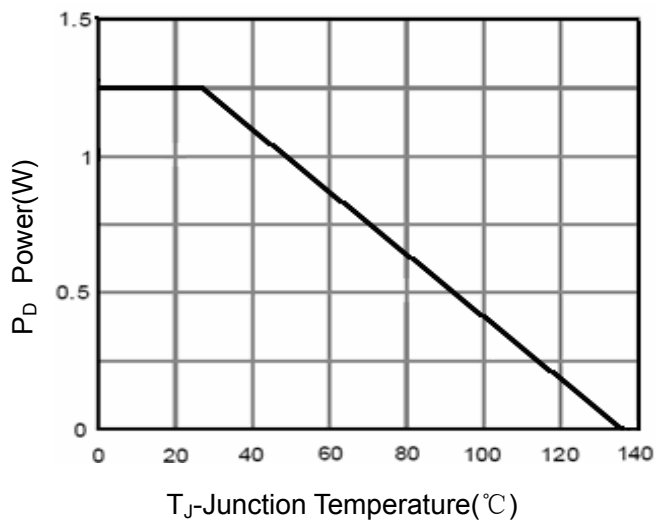


Figure 3 Power Dissipation

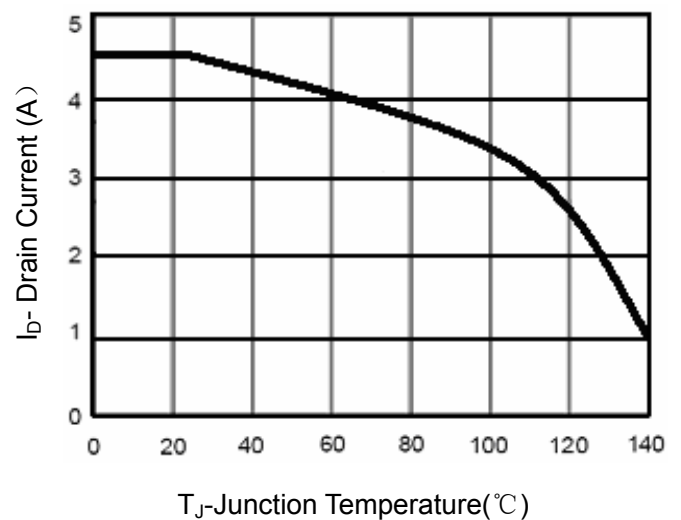


Figure 4 Drain Current

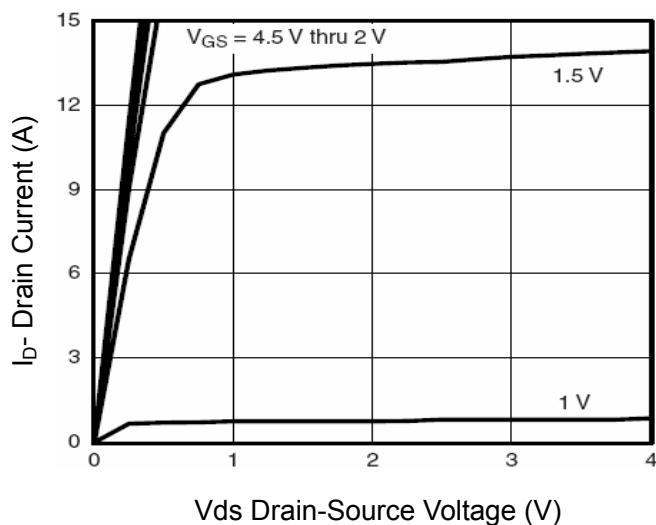


Figure 5 Output CHARACTERISTICS

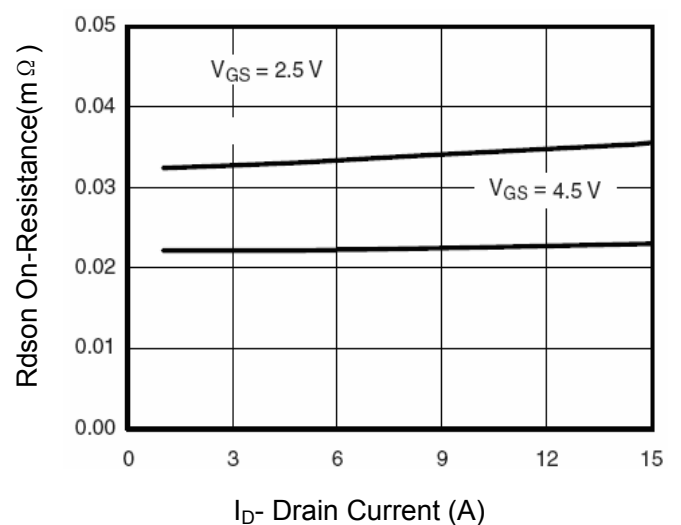


Figure 6 Drain-Source On-Resistance

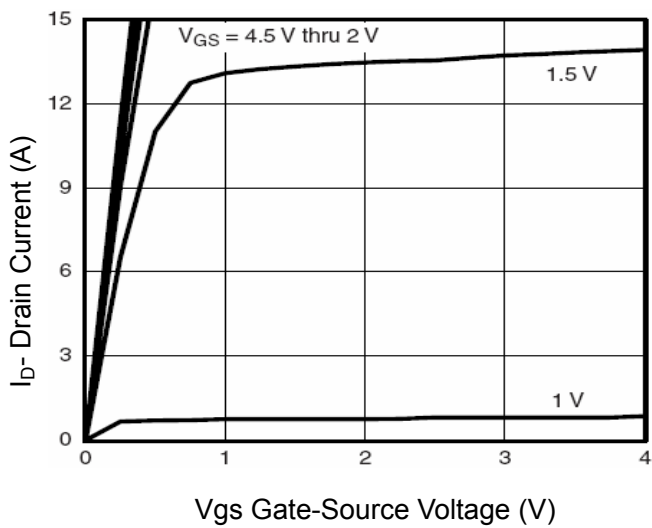


Figure 7 Transfer Characteristics

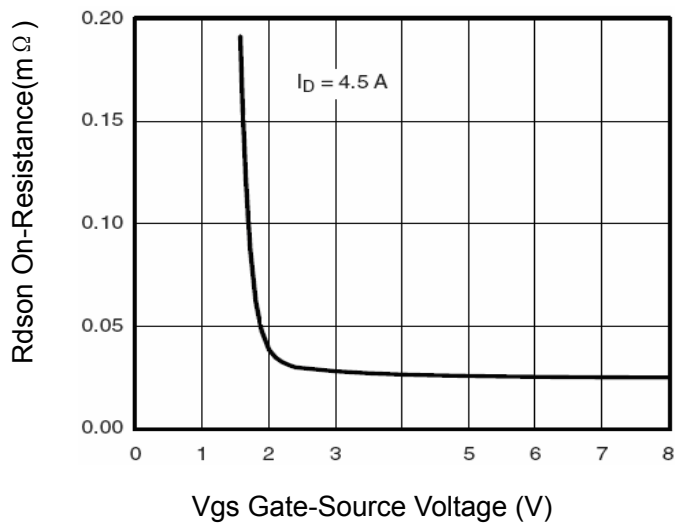


Figure 9 Rdson vs Vgs

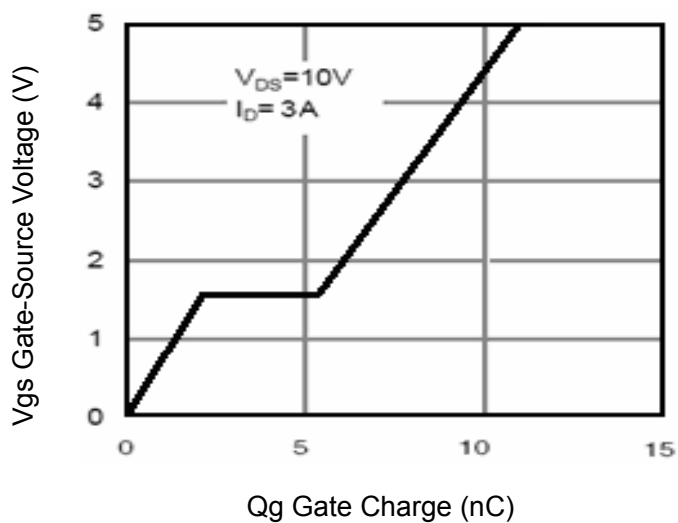


Figure 11 Gate Charge

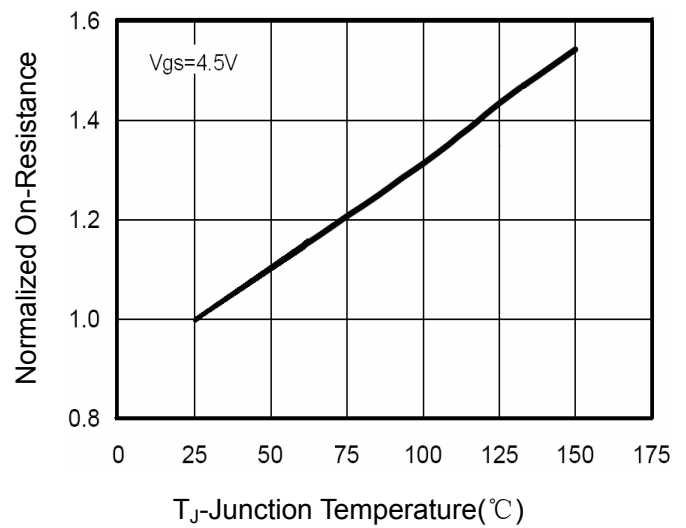


Figure 8 Drain-Source On-Resistance

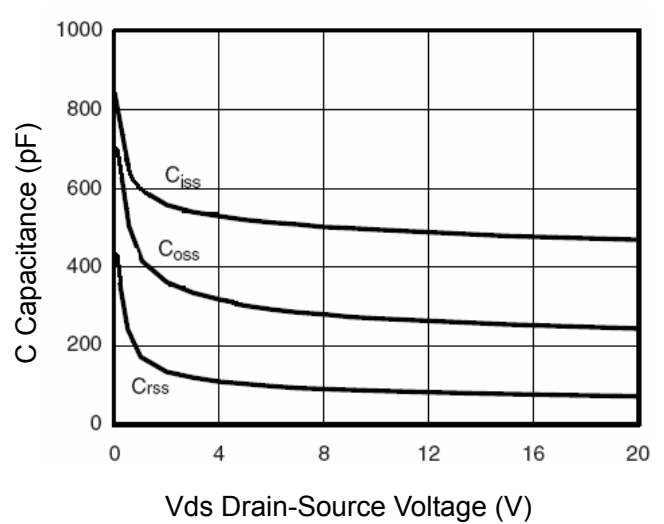


Figure 10 Capacitance vs Vds

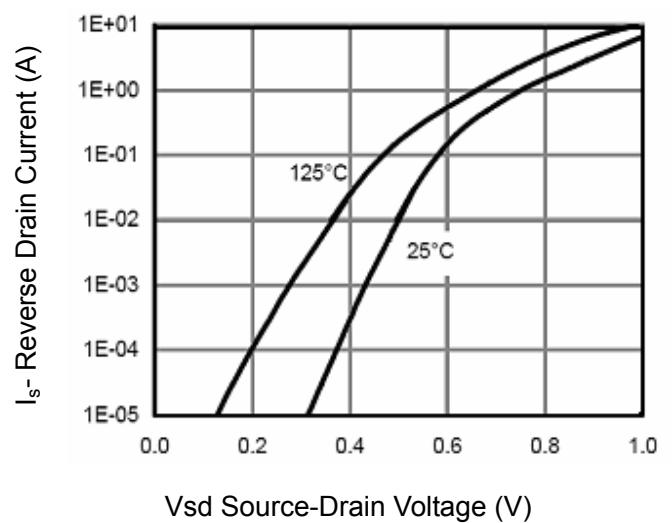


Figure 12 Source- Drain Diode Forward

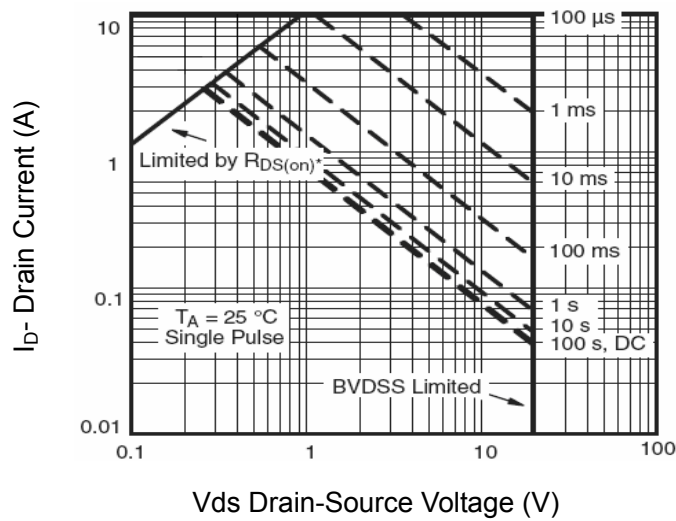


Figure 13 Safe Operation Area

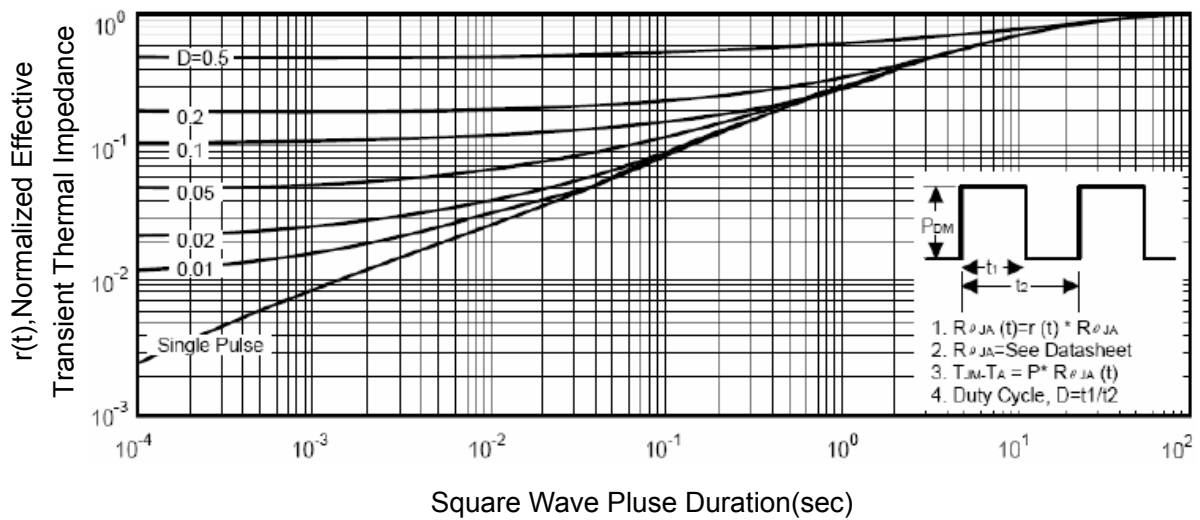
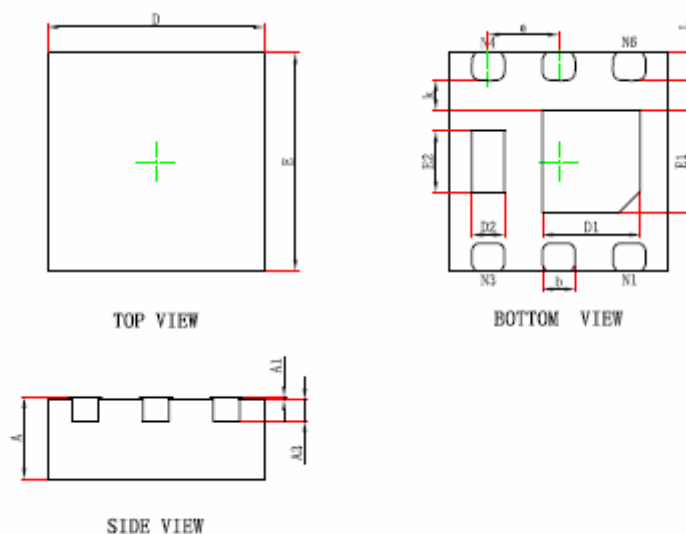


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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